

# SB120 - SB1100

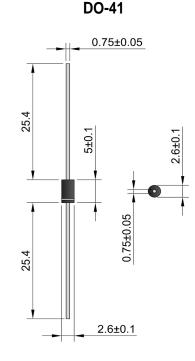
**1.0A SCHOTTKY BARRIER DIODE** 

## Features

- Schottky Barrier Chip
- Guard Ring for Transient and ESD Protection
- Surge Overload Rating to 30A Peak
- Low Power Loss, High Efficiency
- Ideally Suited for Use in High Frequency SMPS, Inverters and As Free Wheeling Diodes

### **Mechanical Data**

- Case: DO-41, Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.35 grams (approx.)
- Mounting Position: Any
- Marking: Type Number
- Lead Free: For RoHS / Lead Free Version



# Maximum Ratings and Electrical Characteristics $@T_A=25^{\circ}C$ unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

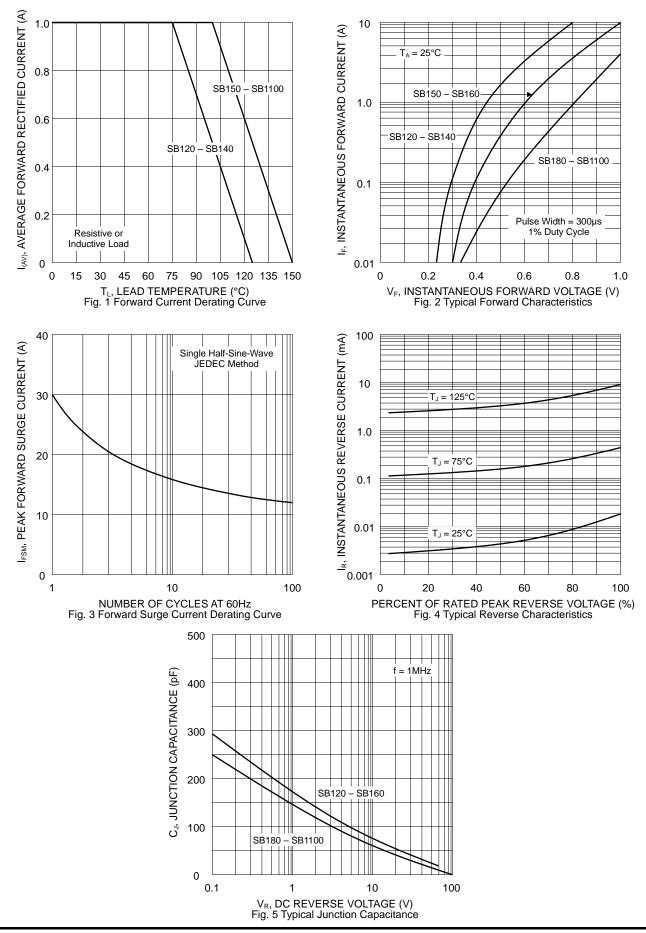
Characteristic	Symbol	SB120	SB130	SB140	SB150	SB160	SB180	SB1100	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	Vrrm Vrwm Vr	20	30	40	50	60	80	100	V
RMS Reverse Voltage	VR(RMS)	14	21	28	35	42	56	70	V
Average Rectified Output Current (Note 1)	lo	1.0							А
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load (JEDEC Method)	IFSM	30							A
Forward Voltage $@I_F = 1.0A$	Vfm	0.50 0.70				0.	85	V	
Peak Reverse Current $@T_J = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_J = 100^{\circ}C$	Irm	0.5 10							mA
Typical Junction Capacitance (Note 2)	Сл	110 80					0	pF	
Thermal Resistance, Junction to Ambient (Note 3) Thermal Resistance, Junction to Lead (Note 3)	R JA R JL	50 15							°C/W
Operating Temperature Range	TJ	-65 to +125 -65 to +150						°C	
Storage Temperature Range	Тѕтс	-65 to +150							°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.

2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

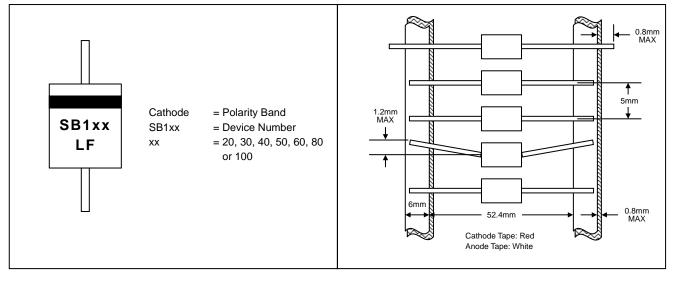
3. Vertical PCB mounting with 12.7mm lead length on 63.5 x 63.5mm copper pad.







### MARKING INFORMATION



**TAPING SPECIFICATIONS** 

#### PACKAGING INFORMATION

